6th Generation CoolSiC[™]

IDH16G65C6



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1 Maximum ratings

Table 3 Maximum ratings

Damanastan	Cb. a.l	Values			11	/
Parameter	Symbol	Min.	Тур.	Max.	Unit	Note/Test condition
	I_F	-	_	16		$T_C \le 135 ^{\circ}\text{C}, D = 1$
Continuous forward current		-	_	18		$T_C \le 125 ^{\circ}\text{C}, D = 1$
		-	-	34		$T_C \le 25 ^{\circ}\text{C}, D = 1$
Surge-repetitive forward current, sine halfwave ¹	$I_{F,RM}$	-	-	70	A	$T_C = 25 ^{\circ}\text{C}, t_p = 10 \text{ms}$
Surge non-repetitive forward	,	_	_	82		$T_C = 25 ^{\circ}\text{C}, t_p = 10 \text{ms}$
current, sine halfwave	$I_{F,SM}$	_	_	65		$T_C = 150 ^{\circ}\text{C}, t_p = 10 \text{ms}$
Non-repetitive peak forward current	I _{F,max}	-	-	710		$T_C = 25 ^{\circ}\text{C}, t_p = 10 \mu\text{s}$
:24	∫ i²dt	_	_	33	A2-	$T_C = 25 ^{\circ}\text{C}, t_p = 10 \text{ms}$
i ² t value		_	_	21	A ² s	$T_C = 150 ^{\circ}\text{C}, t_p = 10 \text{ms}$
Repetitive peak reverse voltage	V_{RRM}	_	-	650	V	<i>T_c</i> = 25 °C
Diode dv/dt ruggedness	dv/dt	_	_	150	V/ns	V _R = 0480 V
Power dissipation	P _{tot}	-	-	97	W	$T_C = 25$ °C, $R_{thJC,max}$
Operating and storage temperature	T_j T_{stg}	-55	-	175	°C	-
Mounting torque	_	_	-	70	Ncm	M3 screw

2 Thermal characteristics

Table 4 Thermal characteristics (PG-TO-220-2)

Parameter	Symbol	Values		Unit	Note/Test condition	
	Symbol	Min.	Тур.	Max.	Uiill	Note/Test condition
Thermal resistance, junction- case	R_{thJC}	_	0.9	1.6	12 /\AI	_
Thermal resistance, junction- ambient	R_{thJA}	_	_	62	K/W	leaded
Soldering temperature, wavesoldering only allowed at leads	T_{sold}	-	-	260	°C	1.6 mm (0.063 in.) from case for 10 s

¹ The surge-repetitive forward current test was performed with 1000 pulses (half-wave rectified sine with the 10 ms period).

Final Datasheet

3 Rev. 2.0, 2017-05-23



3 Electrical characteristics

3.1 Static characteristics

Table 5Static characteristics

Down story	Complete	Values			I I as i to	Note /Tost on with our
Parameter	Symbol	Min.	Min. Typ. Max. Unit Note/Test co	Note/Test condition		
DC blocking voltage	V_{DC}	650	-	_		<i>T_j</i> = 25 °C
Die de femuerd veltere	1/	_	1.25	1.35	٧	$I_F = 16 \text{ A}, T_j = 25 ^{\circ}\text{C}$
Diode forward voltage	V_F	_	1.5	_		$I_F = 16 \text{ A}, T_j = 150 \text{ °C}$
		_	1.6	53		$V_R = 420 \text{ V}, T_j = 25 \text{ °C}$
Reverse current	I_R	_	53	_	μΑ	$V_R = 420 \text{ V}, T_j = 125 \text{ °C}$
		_	123	_		V_R = 420 V, T_j = 150 °C

3.2 AC characteristics

Table 6 AC characteristics

Deve mester.	Complete		Values		l lmit	Unit Note/Test Condition		
Parameter	Symbol	Min.	Тур.	Max.	Unit	Jnit Note/Test Condition		
Total capacitive charge	Q_c	_	21.5	-	nC	V_R = 400 V, T_j = 150 °C, di/dt = 200 A/ μ s, $I_F \le I_{F,MAX}$		
		-	783	-		$V_R = 1 \text{ V, } f = 1 \text{ MHz,}$ $T_j = 25 \text{ °C}$		
Total capacitance	С	_	46	-	pF	$V_R = 300 \text{ V}, f = 1 \text{ MHz},$ $T_j = 25 \text{ °C}$		
		_	44	_		V_R = 600 V, f = 1 MHz, T_j = 25 °C		



4 Diagrams

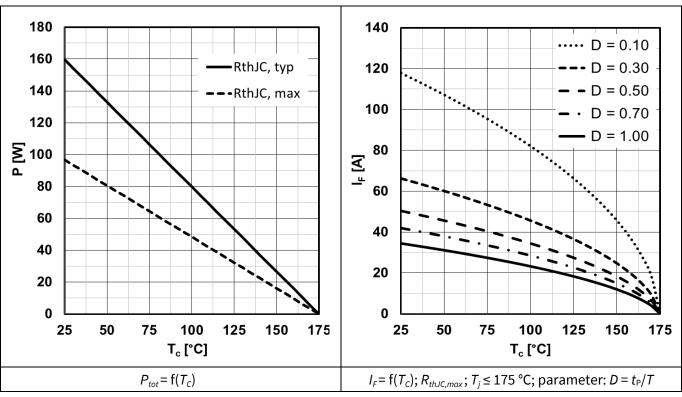


Figure 1 Power dissipation

Figure 2 Max. forward current

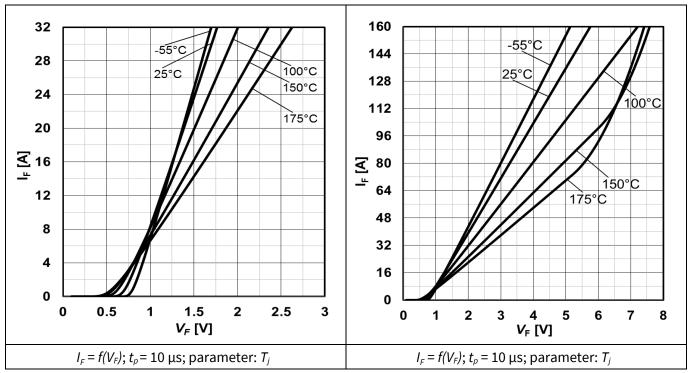


Figure 3 Typ. forward characteristics

Figure 4 Typ. forward characteristics in surge current



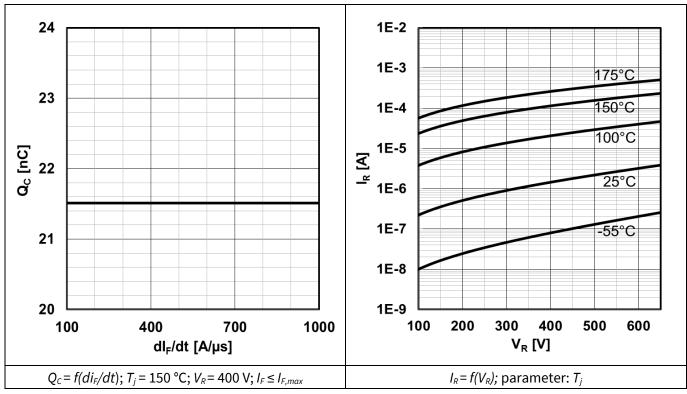


Figure 5 Typ. cap. charge vs. current slope

Figure 6 Typ. reverse current vs. reverse voltage

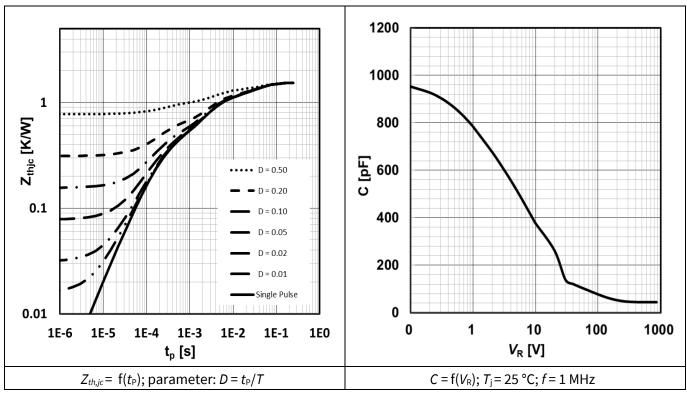


Figure 7 Max. transient thermal impedance

Figure 8 Typ. capacitance vs. reverse voltage



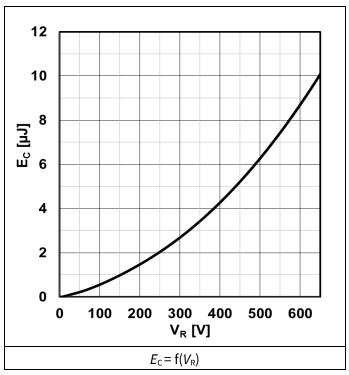


Figure 9 Typ. capacitance stored energy

5 Simplified forward characteristic

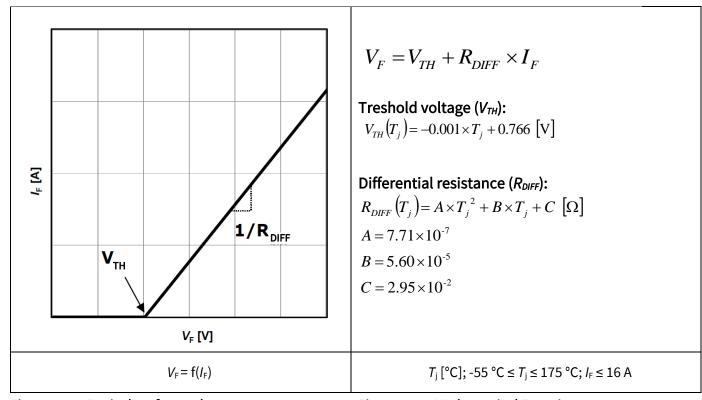


Figure 10 Equivalent forward current curve

Figure 11 Mathematical Equation



6 Package outlines

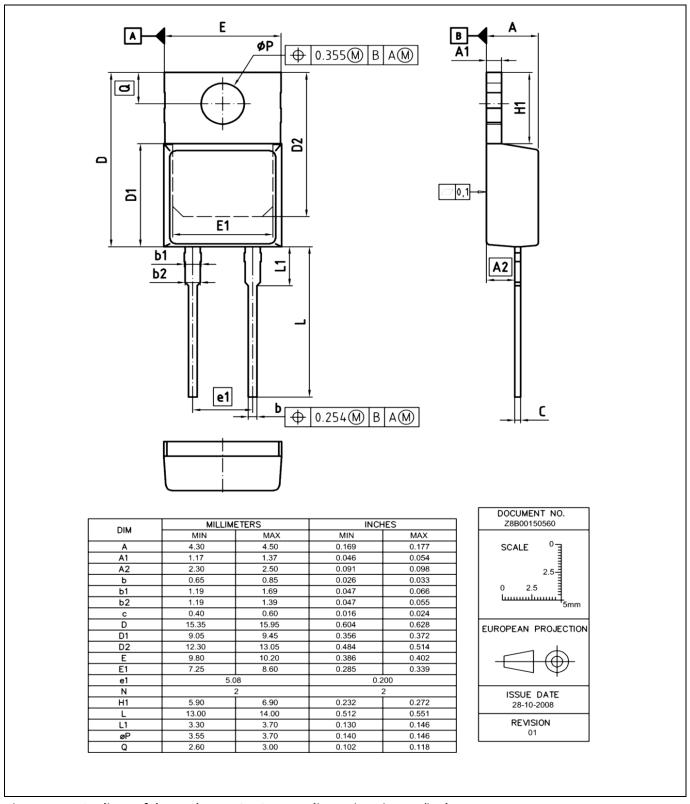


Figure 12 Outlines of the package PG-TO220-2, dimensions in mm/inches

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Revision History

Major changes since the last revision

Revision	Date	Subject (major changes since last revision)					
2.0	2017-05-23	Release of final version					

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